

Amendments to the Claims:

The following listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1. (currently amended) ~~Radiation-emitting~~ A radiation-emitting semiconductor component ~~having~~ comprising:

a semiconductor body (1), ~~which has~~ comprising an active zone (2);

~~in which, for the purpose of electrical contact connection,~~ a patterned contact layer (3) ~~is~~ applied on a surface of the semiconductor body for electrical contact connection[[.]];

interspaces (4) distributed over the contact layer (3) ~~being provided~~ for the purpose of forming free areas (5) on the surface which are not covered by the contact layer (3), ~~in which free areas (5) are covered with a mirror (6); and~~

a mirror for covering the free areas.

2. (currently amended) ~~Component~~ The component according to claim 1, in which the mirror (6) is embodied as a closed mirror layer (7) covering the free areas (5) and the contact layer (3).

3. (currently amended) ~~Component~~ The component according to claim 2, in which the material of the contact layer (3) links electrically better to the semiconductor body (1) than the material of the mirror layer (7).

4. (currently amended) ~~Component~~ The component according to claim 2, in which the material of the mirror layer (~~7~~) reflects the radiation generated in the active zone (~~2~~) better than the material of the contact layer (~~3~~).

5. (currently amended) ~~Component~~ The component according to claim 1, in which the surface of the semiconductor body (~~1~~) is formed by a p-doped layer (~~8~~) made of a nitride compound semiconductor, and in which the material of the contact layer (~~3~~) forms an ohmic contact with respect to the surface.

6. (currently amended) ~~Component~~ The component according to claim 1, in which the contact layer (~~3~~) contains platinum or nickel.

7. (currently amended) ~~Component~~ The component according to claim 2, in which the mirror layer (~~7~~) contains silver or aluminium.

8. (currently amended) ~~Component~~ The component according to claim 1, in which the contact layer (~~3~~) has a thickness (~~d~~) which is less than 100 nm.

9. (currently amended) ~~Component~~ The component according to claim 1, in which the contact layer (~~3~~) comprises contact elements (~~9~~) that are separated from one another, and in which a connecting layer (~~10~~) for making contact among the contact elements (~~9~~) is provided on the contact layer (~~3~~).

10. (currently amended) ~~Component~~ The component according to claim 9, in which the contact elements (9) have the form of cylinders.

11. (currently amended) ~~Component~~ The component according to claim 9, in which the contact elements (9) are arranged at the nodes of a regular grid.

12. (currently amended) ~~Component~~ The component according to claim 11, in which the regular grid is a square grid.

13. (currently amended) ~~Component~~ The component according to claim 9, in which the surface of the semiconductor body is formed by a p-doped layer made of a nitride compound semiconductor, the p-doped layer having a surface which faces the active zone and constitutes an interface, wherein the distances (D1, D2) distance between the every two adjacent contact elements (9) are chosen taking account of is related to the transverse conductivity of the p-doped layer (8) such that the semiconductor body's entire interface (11) of the p-doped layer (8) can be energized over the whole area.

14. (canceled)

15. (currently amended) ~~Component~~ The component according to claim 14 ~~11~~, in which the regular grid is a hexagonal grid.

16. (currently amended) ~~Component~~ The component according to claim 1, in which the interspaces ~~(4)~~ are filled with a filler ~~(12)~~ in order to at least partially planarize the surface of the patterned contact layer ~~(3)~~.

17. (currently amended) ~~Component~~ The component according to claim 16, in which the filler ~~(12)~~ contains an electrically conductive material.

18. (currently amended) ~~Component~~ The component according to claim 16, in which the filler ~~(12)~~ contains a transparent and electrically insulating material.

19. (currently amended) ~~Component~~ The component according to claim 17, in which the filler ~~(12)~~ contains zinc oxide or indium tin oxide.

20. (currently amended) ~~Component~~ The component according to claim 18, in which the filler ~~(12)~~ contains SiO₂, a compound made of silicon and nitrogen or titanium oxide or plastic.

21. (currently amended) ~~Component~~ The component according to claim 16, in which the filler ~~(12)~~ forms Bragg reflectors ~~(13)~~.

22. (currently amended) ~~Component~~ The component according to claim 21, in which the Bragg reflectors ~~(13)~~ are produced from dielectrics.

23. (currently amended) ~~Component~~ The component according to claim 21, in which the Bragg reflectors ~~(13)~~ are produced by epitaxy.

24. (currently amended) ~~Component~~ The component according to claim 1, in which the mirror ~~(6)~~ is formed by Bragg reflectors ~~(13)~~ arranged in the interspaces ~~(4)~~ of the contact layer ~~(3)~~.

25. (currently amended) ~~Component~~ The component according to claim 24, in which the Bragg reflectors ~~(13)~~ contain layer pairs ~~(14)~~ lying one on top of the other, of which respectively one has a high refractive index and one has a low refractive index, and in which a number greater than 5 of layer pairs ~~(14)~~ are provided in each Bragg reflector ~~(13)~~.